SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

Large current, surface mount device.

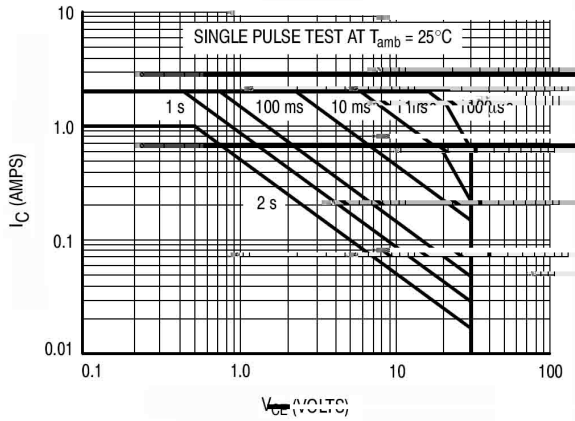
Switching for high current applica-5em.3.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-1.0	A
Collector Current − Peak	I_{CM}	-2.0	A
Collector Power Dissipation	P_D	310	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

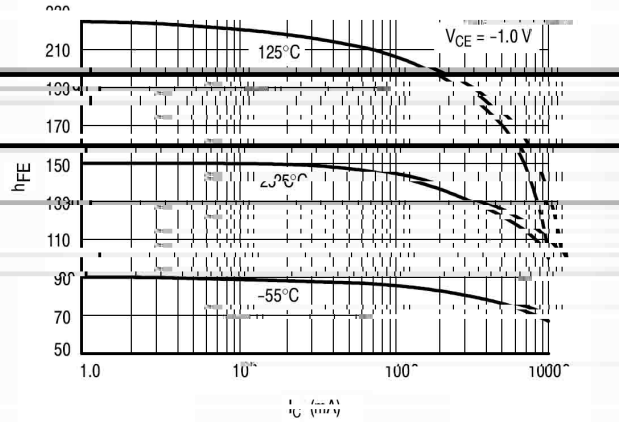
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-10mA I_B=0	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V I_E=0			-0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-4.0V I_E=0			-0.1	μA
Collector−Emitter Cutoff Current	I_{CES}	V_{CES}=-30V I_E=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-500mA	100		300	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-2.0A	40			
	$h_{FE(3)}$	V_{CE}=-2.0V I_C=-1.0A	80			
	$h_{FE(4)}$	V_{CE}=-2.0V I_C=-1.0mA	100			
Collector −Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-500mA I_B=-50mA			-0.25	V
	$V_{CE(sat)(2)}$	I_C=-1.0A I_B=-100mA			-0.30	V
	$V_{CE(sat)(3)}$	I_C=-2.0A I_B=-200mA			-0.65	V
Base−Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-1.0A I_B=-0.1A			-1.2	V
Base−Emitter Turn−on Voltage	$V_{BE(ON)}$	I_C				

/ Electrical Characteristic Curve

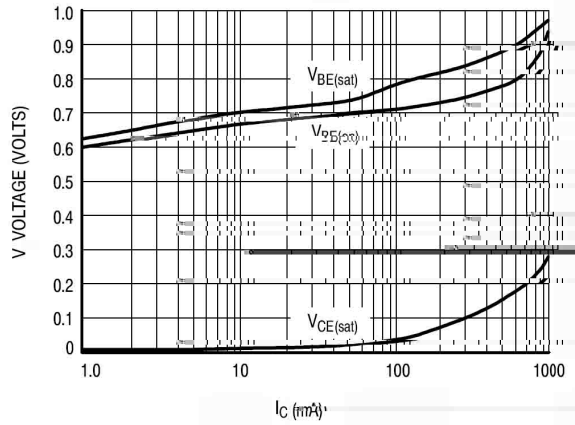
I_C — V_{CE}



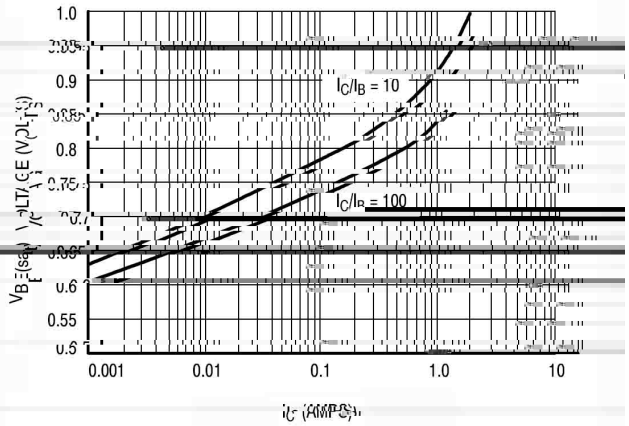
h_{FE} — I_C



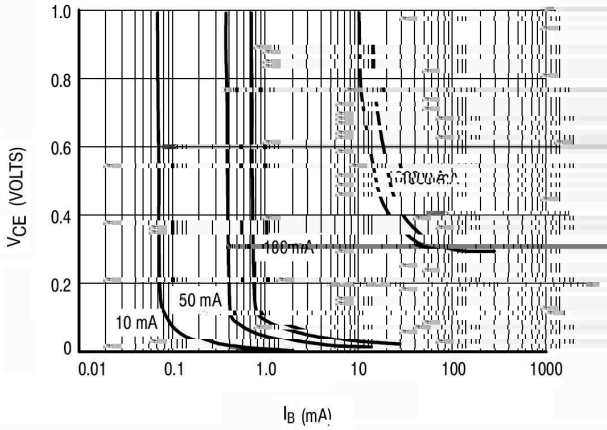
V — I_C



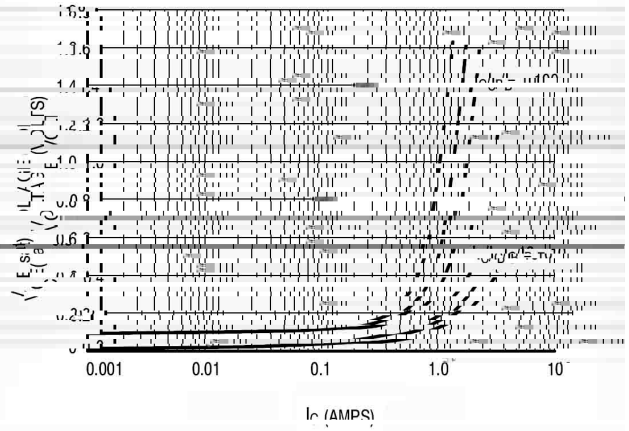
$V_{BE(sat)}$ — I_C



V_{CE} — I_B

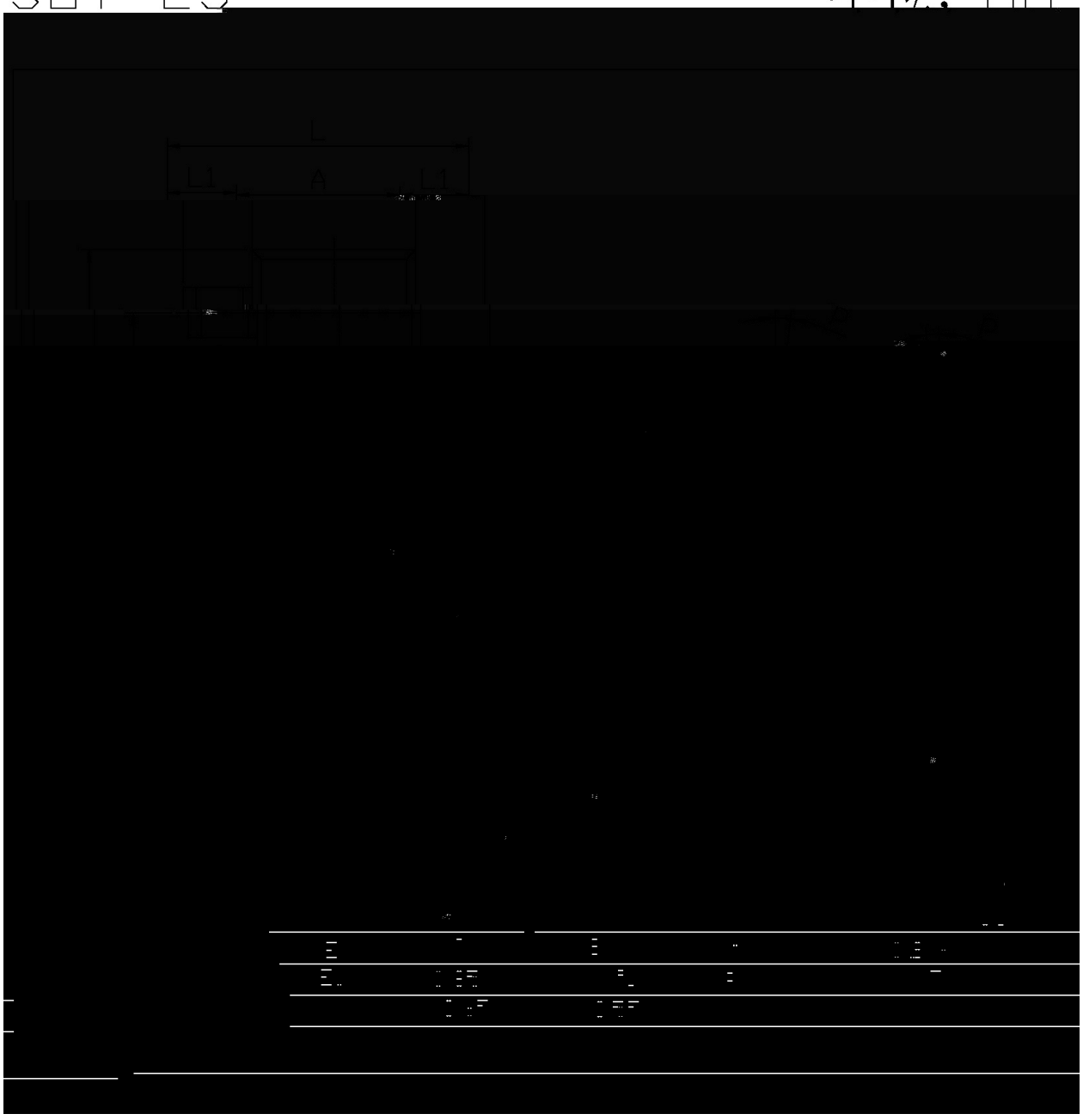


$V_{CE(sat)}$ — I_C

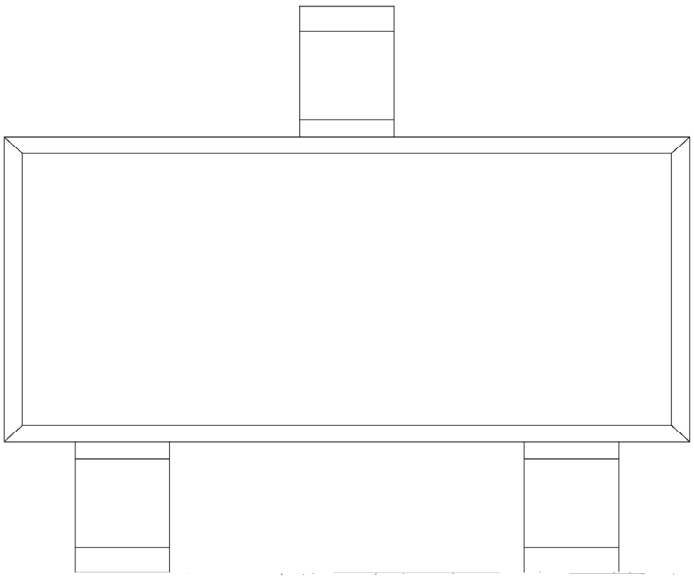


/ Package Dimensions

SOT-23 单位：mm



/ Marking Instructions



H

G3

Note: